

MAC16CD, MAC16CM, MAC16CN

Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full-wave, silicon gate-controlled devices are needed.

- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability — 150 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- Operational in Three Quadrants, Q1, Q2, and Q3
- Device Marking: Logo, Device Type, e.g., MAC16CD, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ (T _J = -40 to 125°C)	V _{DRM} , V _{RPM}	400 600 800	Volts
On-State RMS Current (Full Cycle Sine Wave 50 to 60 Hz; T _C = 80°C)	I _{T(RMS)}	16	A
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _J = 125°C)	I _{TSM}	150	A
Circuit Fusing Consideration (t = 8.33 ms)	I ² t	93	A ² sec
Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C)	P _{GM}	20	Watts
Average Gate Power (t = 8.3 ms, T _C = 80°C)	P _{G(AV)}	0.5	Watts
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

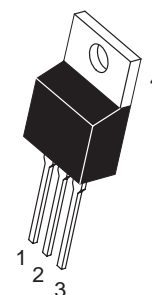
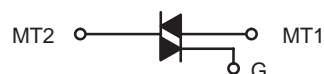
(1) V_{DRM} and V_{RPM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor

<http://onsemi.com>

TRIACS
16 AMPERES RMS
400 thru 800 VOLTS



TO-220AB
CASE 221A
STYLE 4

PIN ASSIGNMENT	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
MAC16CD	TO220AB	50 Units/Rail
MAC16CM	TO220AB	50 Units/Rail
MAC16CN	TO220AB	50 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.2 62.5	$^{\circ}C/W$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}$ Gate Open)	I_{DRM}, I_{RRM}	— —	— —	0.01 2.0	mA
		$T_J = 25^{\circ}C$			
		$T_J = 125^{\circ}C$			

ON CHARACTERISTICS

Peak On-State Voltage ⁽¹⁾ ($I_{TM} = \pm 21$ A Peak)	V_{TM}	—	1.2	1.6	V
Gate Trigger Current (Continuous dc) ($V_D = 12$ V, $R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	I_{GT}	8.0 8.0 8.0	12 16 20	35 35 35	mA
Holding Current ($V_D = 12$ V, Gate Open, Initiating Current = ± 150 mA)	I_H	—	20	50	mA
Latching Current ($V_D = 12$ V, $I_G = 35$ mA) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	I_L	— — —	25 40 24	50 80 50	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12$ V, $R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	V_{GT}	0.5 0.5 0.5	.75 .72 .82	1.5 1.5 1.5	V

DYNAMIC CHARACTERISTICS

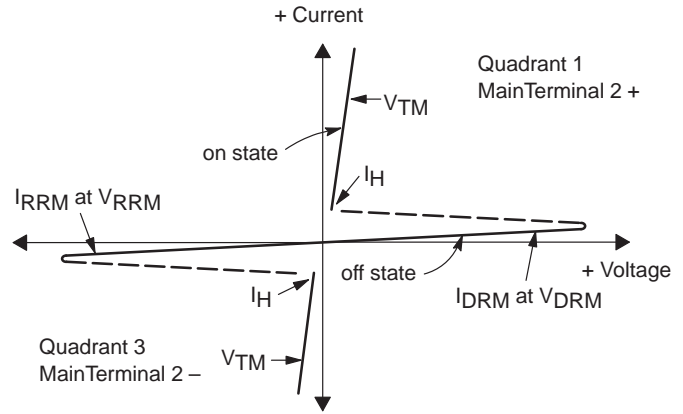
Rate of Change of Commutating Current ($V_D = 400$ V, $I_{TM} = 6.0$ A, Commutating $dv/dt = 24$ V/ μ s, Gate Open, $T_J = 125^{\circ}C$, $f = 250$ Hz, $C_L = 10 \mu F$, $L_L = 40$ mH, with Snubber)	$(di/dt)_C$	15	—	—	A/ms
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 125^{\circ}C$)	dv/dt	600	—	—	V/ μ s
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 μ sec; $diG/dt = 200$ mA/ μ sec; $f = 60$ Hz	di/dt	—	—	10	A/ μ s

(1) Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle $\leq 2\%$.

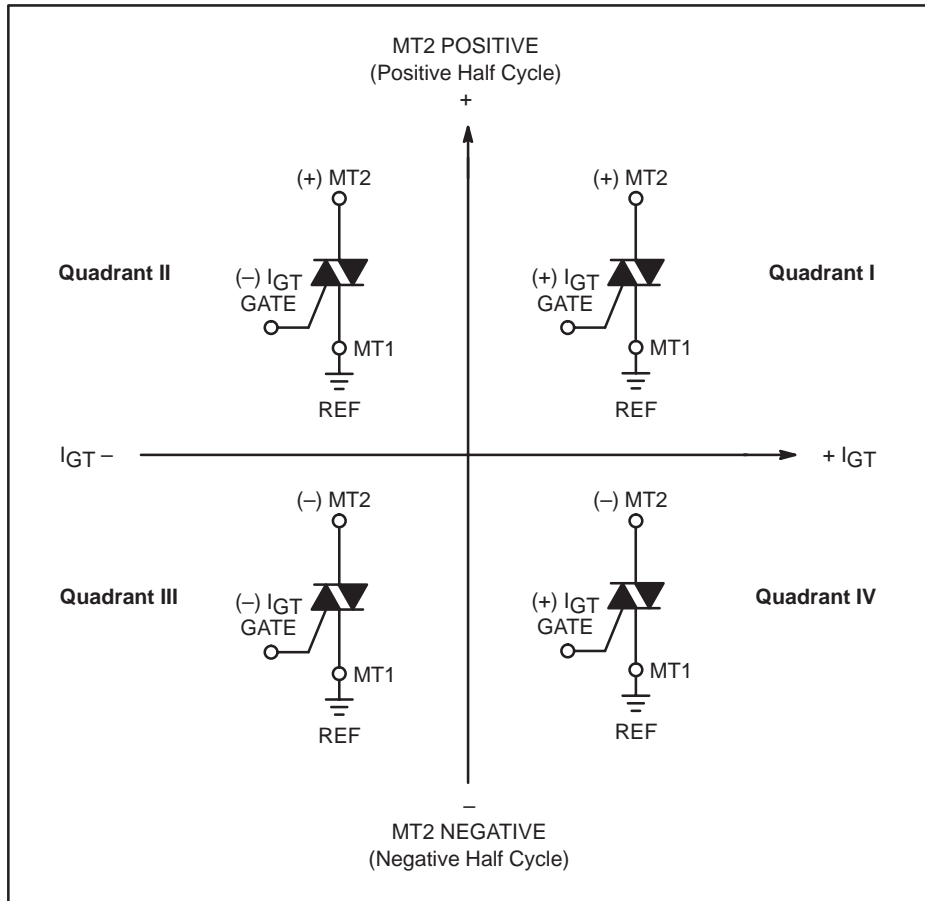
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Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used.

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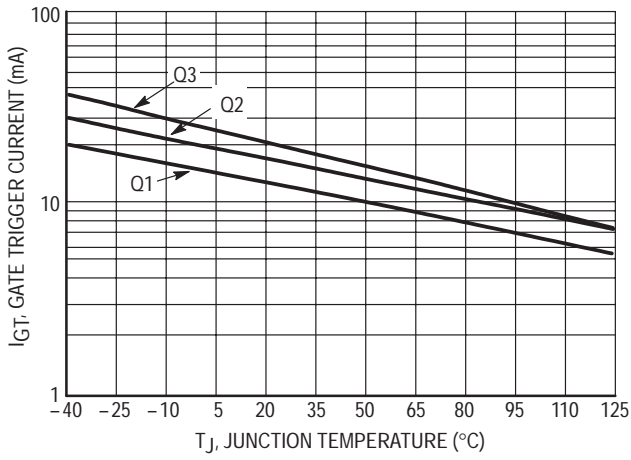


Figure 1. Typical Gate Trigger Current versus Junction Temperature

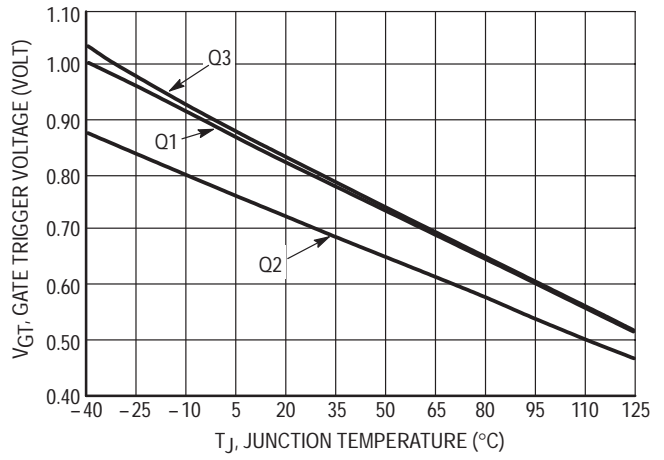


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

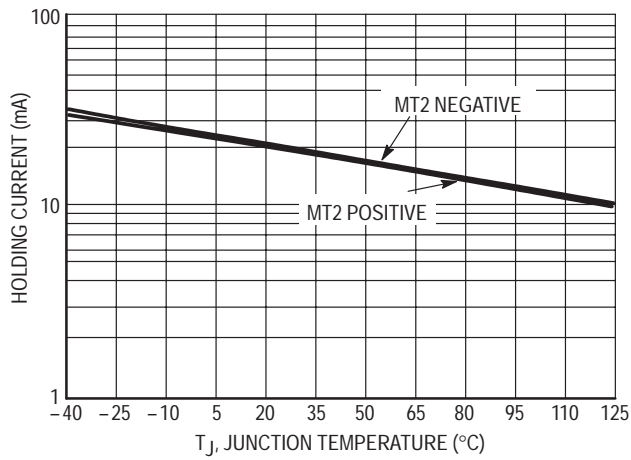


Figure 3. Typical Holding Current versus Junction Temperature

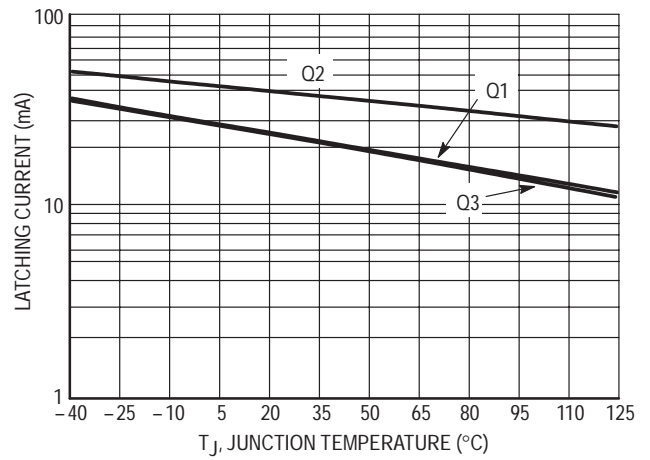


Figure 4. Typical Latching Current versus Junction Temperature

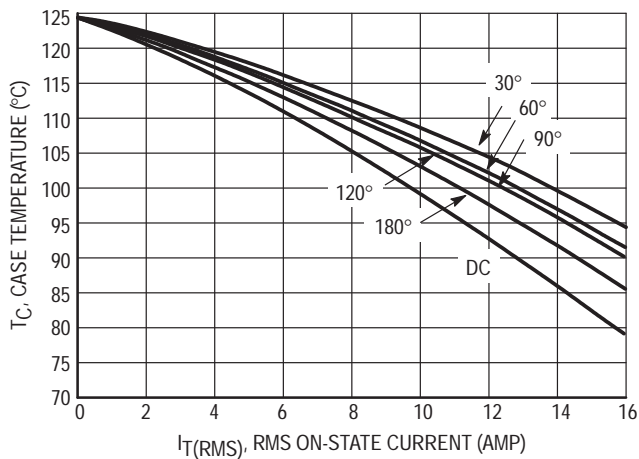


Figure 5. Typical RMS Current Derating

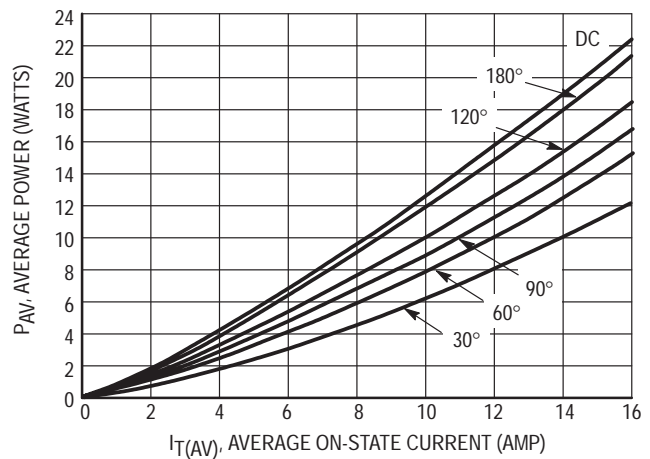


Figure 6. On-State Power Dissipation

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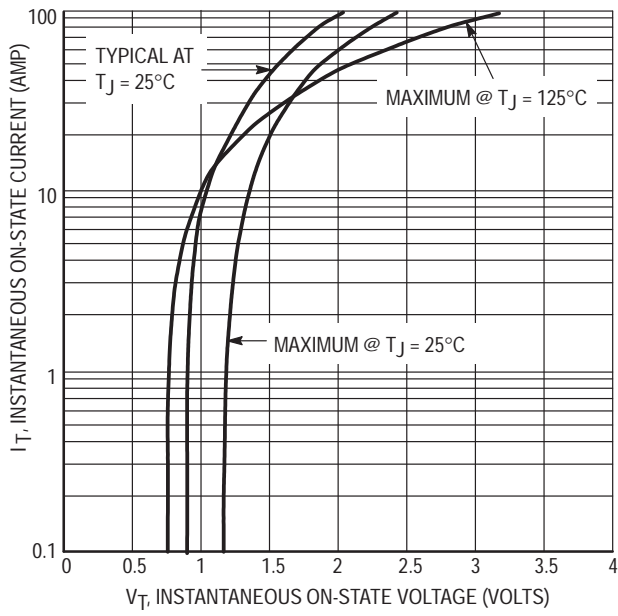


Figure 7. On-State Characteristics

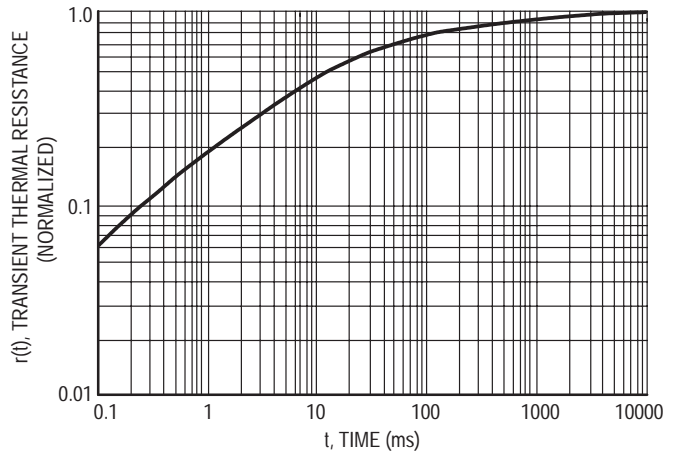


Figure 8. Typical Thermal Response